



PTD928G/PTU928G

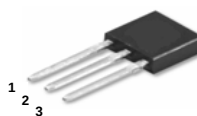
PNP Epitaxial Silicon Transistor

- 3 Amperes / 15 Watts

Audio Power Amplifier

- Low speed switching

PTU928G I-PAK(TO-251)



1. Base
2. Collector
3. Emitter

PTD928G D-PAK(TO-252)



1. Base
2. Collector
3. Emitter

Absolute Maximum Ratings $T_A=25^{\circ}\text{C}$ unless otherwise noted

CHARACTERISTICS	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-55	V
Emitter-Base Voltage	V_{EBO}	-7.0	V
Collector Current (DC)	I_C	-3.0	A
Collector Dissipation ($T_c=25^{\circ}\text{C}$)	P_C	15	W
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~150	$^{\circ}\text{C}$

Electrical Characteristics $T_A=25^{\circ}\text{C}$ unless otherwise noted

CHARACTERISTICS	SYMBOL	Test Condition	Min	Typ.	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=-100\mu\text{A}, I_E=0$	-60	--	--	V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=-1\text{mA}, I_B=0$	-55	--	--	V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_C=-100\mu\text{A}, I_E=0$	-7	--	--	V
Collector Cut-off Current	I_{CBO}	$V_{EB}=-60\text{V}, I_C=0$	--	--	-500	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$	--	--	-500	nA
DC Current Gain	h_{FE}	$V_{CE}=-2\text{V}, I_C=-1.0\text{A}$	120	--	320	--
*Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-2.0\text{A}, I_B=-0.2\text{A}$	--	-0.4	-0.55	V
*Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-2.0\text{A}, I_B=-0.2\text{A}$	--	-1.0	-1.5	V
Output Capacitance	C_{ob}	$V_{CB}=-10\text{V}, f=1\text{MHz}$	--	48	--	pF
Current Gain Bandwidth Product	f_T	$V_{CE}=-2\text{V}, I_C=-0.5\text{A}$	--	120	--	MHz

* Pulse Test : Pulse Width $\leq 250\mu\text{s}$, Duty Cycle $\leq 2\%$

Typical Characteristics

